

In the Specification:

Please amend paragraph [0006] as follows:

Most photolithography masks employ two primary layers: (1) a transparent, e.g., glass, substrate layer having high light transmittance; and (2) a masking, opaque layer having a lower transmittance. Depending upon the type of photolithographic mask, of which there are several, the transmittance of the opaque layer may actually be other than non-zero. In certain attenuated phase shift masks, for example, the opaque attenuator layer may have a transmittance of approximately 6%. Other phase shift masks may have different transmission, such as a high transmittance of 17%, for one example.

Please amend paragraph [0016] as follows:

An embodiment of another aspect of the present invention is a photolithography mask for use in the fabrication of integrated circuits. The photolithography mask comprises a first layer and also has a second layer with a primary and substantially constant thickness as well as a region of un-altered ~~altered~~ thickness, the altered thickness causing a pre-selected phase shift in light passing through it relative to the phase of light incident upon the region of altered thickness. In this embodiment, the region of altered thickness in the second layer is not a penetration through or hole formed in the second layer.

Please amend paragraph [0027] as follows:

According to an aspect of the present invention, a repair process for a phase shift mask involves matching both the transmission as well as the phase of the surrounding masking material. The process, without limitation, introduces a phase shift error at the future repair site prior to deposition of the repair material. This way, the combined phase and transmission effect of the repaired ~~repair~~-location matches the surrounding ~~[[the]]~~ opaque layer, whether MoSi.sub.2 or other material, in terms of optical behavior and does not cause critical dimension variations on the wafer.